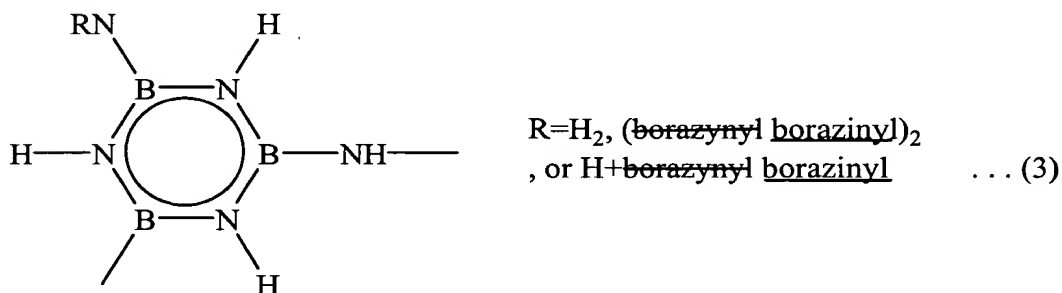
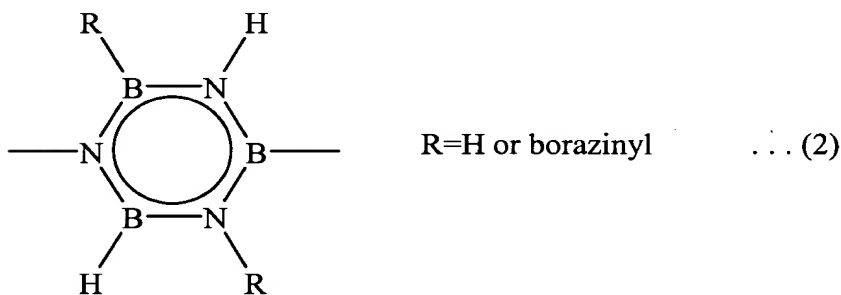
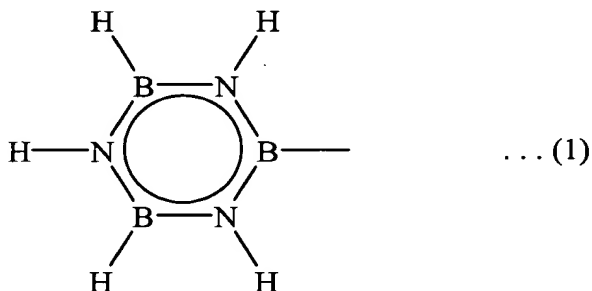


IN THE CLAIMS

Please amend the claims as follows:

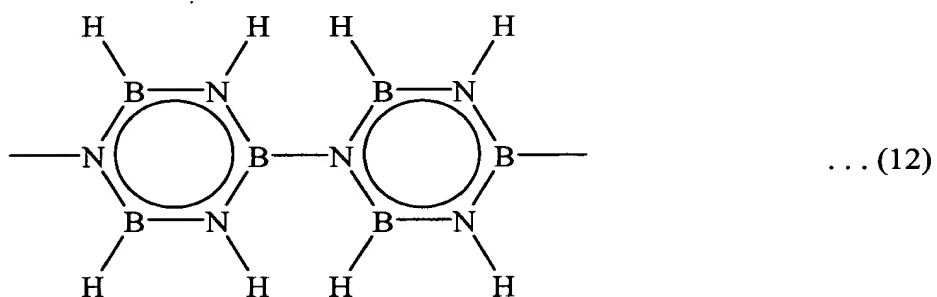
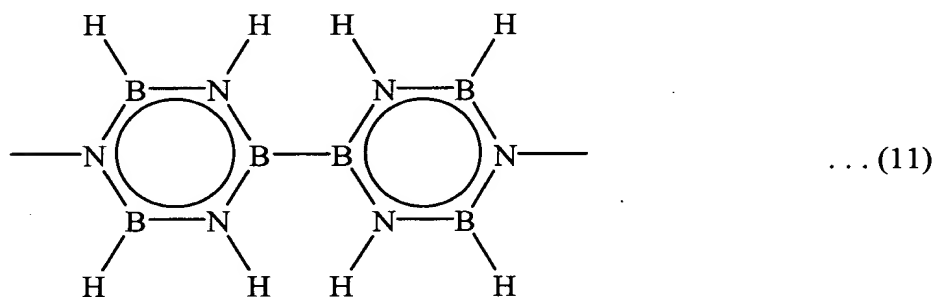
Claim 1 (Currently Amended): ~~A low dielectric constant material having thermal resistance,~~ An insulation film for use between semiconductor layers, comprising borazine ~~skeletal molecules~~ moieties shown by the following formula (1), (2), or (3) ~~in as part of an inorganic or organic material molecule,~~ wherein said film has a dielectric constant of at most 2.4 and a thermal resistance of at least 450°C.

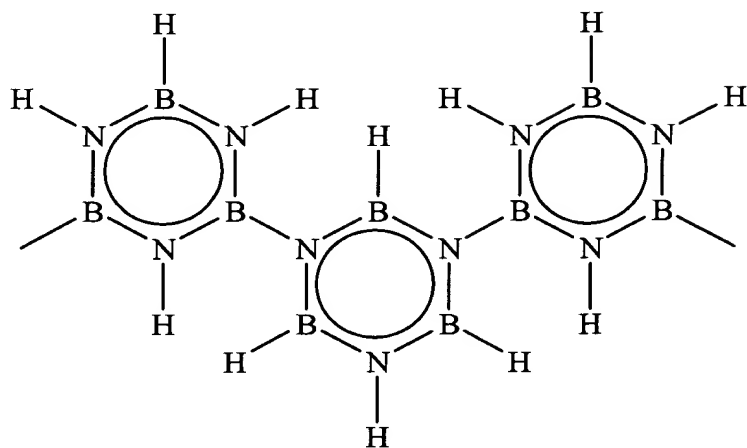


Claim 2 (Canceled).

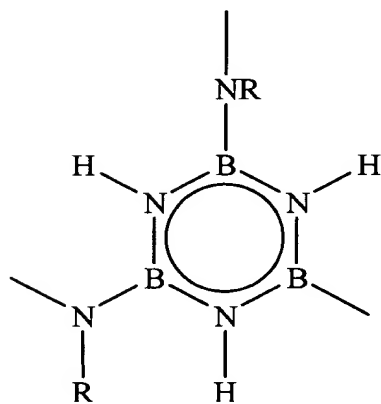
Claim 3 (Currently Amended): A semiconductor device, comprising ~~an~~ the insulation film ~~between semiconductor layers comprising the low dielectric constant material having thermal resistance of Claim 1, between semiconductor layers.~~

Claim 4 (New): The insulation film of Claim 1, wherein said molecule contains at least one moiety selected from the following formulae (11) – (17):



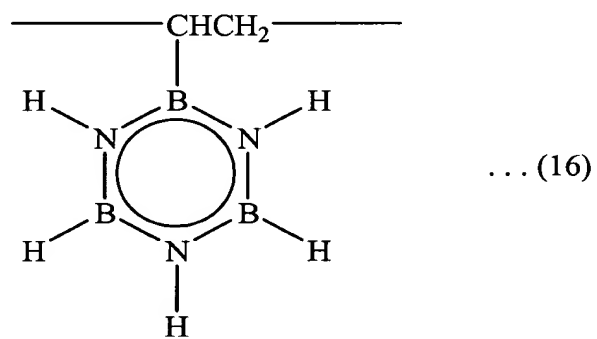
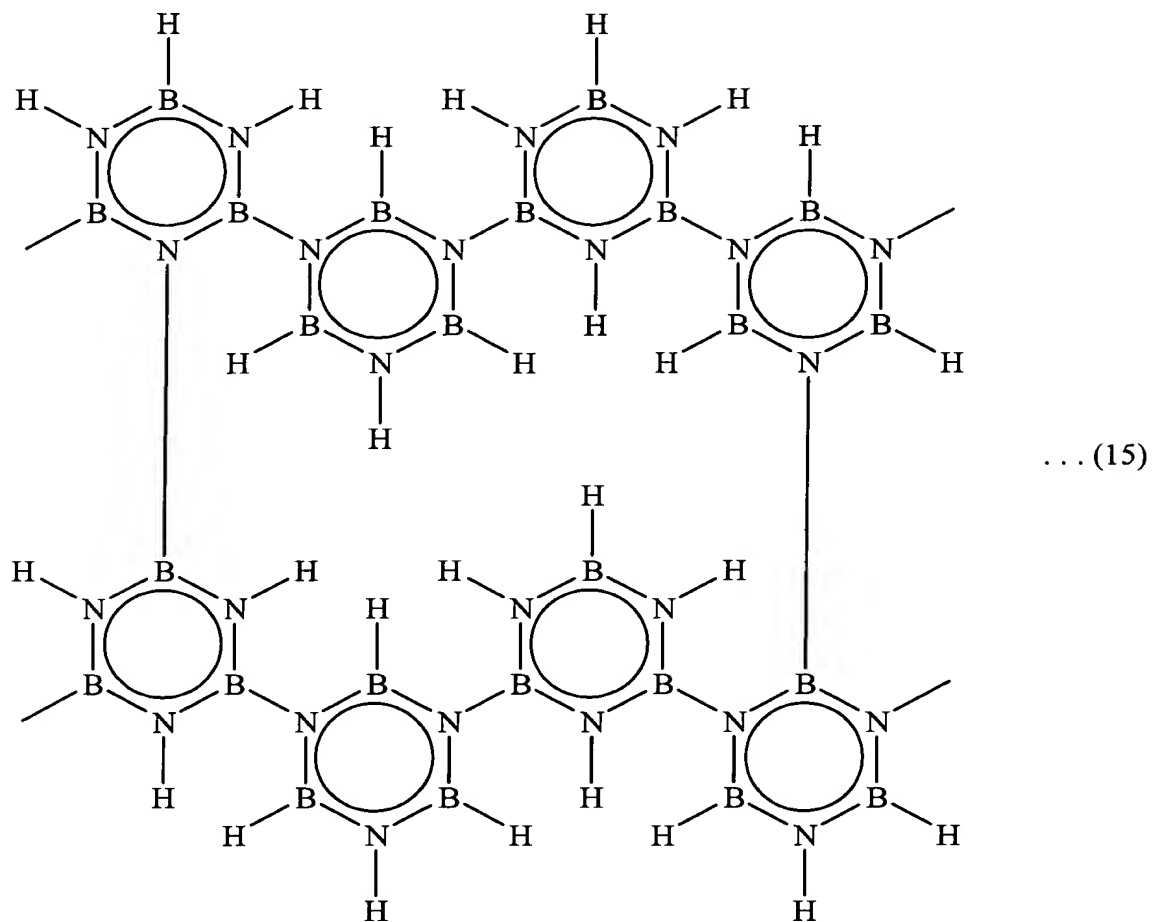


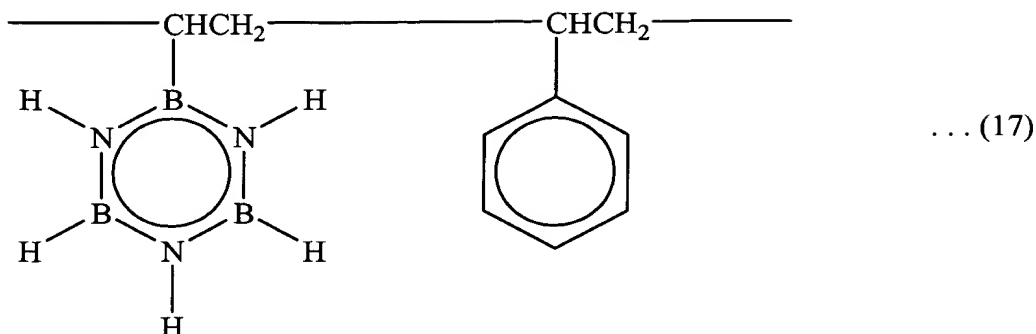
... (13)



R=H or borazinyl

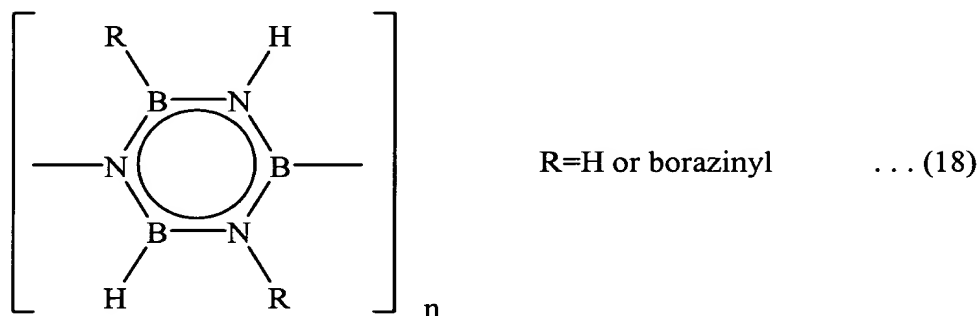
... (14)





Claim 5 (New) The insulation film material of Claim 1, wherein the inorganic material is selected from the group consisting of silicates, silazanes, silsequioxanes, siloxanes, and silanes, and the organic material is selected from the group consisting of poly(aryl ether), parylene, polyphenylene, polyphenylenevinylene, and polybenzocyclobutene.

Claim 6 (New): A film comprising a material having the following formula (18):



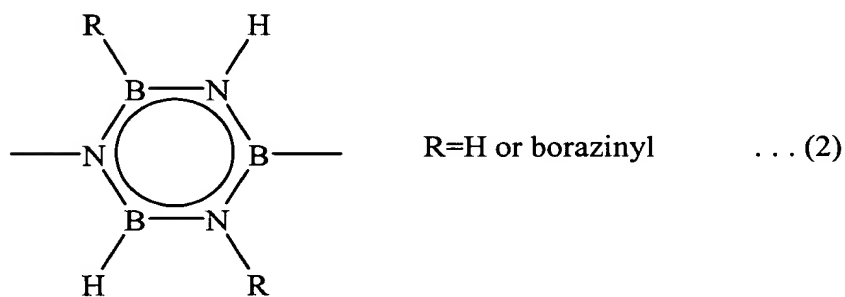
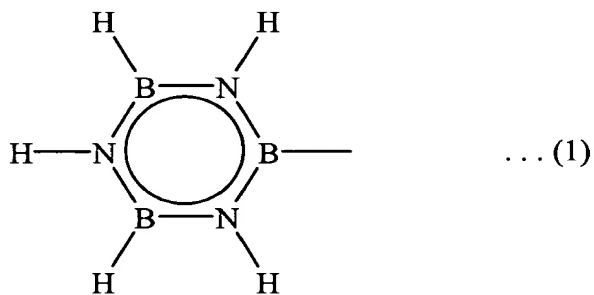
wherein n is an integer, and having a gold electrode deposited thereon, wherein said material may be partially crosslinked.

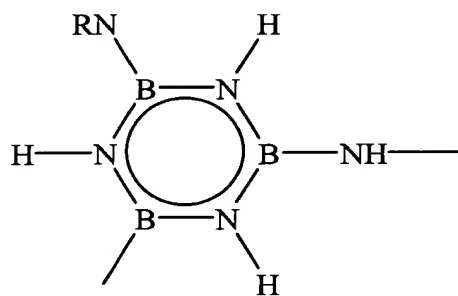
Claim 7 (New): A film comprising poly(aminoboraziny) having a gold electrode deposited thereon, wherein the poly(aminoboraziny) is partially crosslinked.

Claim 8 (New): A film comprising poly(B-vinylborazine), and having a gold electrode deposited thereon, wherein the poly(B-vinylborazine) is partially crosslinked.

Claim 9 (New): A film comprising a poly(styrene-co-B-vinylborazine), and having a gold electrode deposited thereon, wherein the poly(styrene-co-B-vinylborazine) is partially crosslinked.

Claim 10 (New): A process for making a semiconductor device, comprising applying an insulation film between semiconductor layers, wherein the insulation film comprises a material having a dielectric constant of at most 2.4 and a thermal resistance of at least 450°C, and wherein the material comprises borazine moieties shown by the following formula (1), (2), or (3) as part of an inorganic or organic material molecule:





R=H<sub>2</sub>, (borazinyl)<sub>2</sub>  
 , or H+borazinyl . . . (3)

DISCUSSION OF THE AMENDMENT

Claim 1 has been amended by incorporating the subject matter of Claim 2 therein; by inserting dielectric constant and thermal resistance limitations as supported in the specification at the paragraph bridging pages 15 and 16; by replacing the word "skeletal molecules" with the more accurate --moieties--; by correcting the spelling of --boraziny--; and by replacing "in" with --as part of--, to clarify that the recited moieties are part of the inorganic or organic molecule. Claim 2 has been canceled. Claim 3 has been amended to be consistent with the amendment to Claim 1.

New Claims 4-10 have been added. Claim 4 is supported by the formulae disclosed at pages 9-11 of the specification. Claim 5 is supported in the specification at page 8, line 25 through page 9, line 1. Claims 6-9 are supported by Examples 1-4, respectively. Claim 10 is drawn to a method of making a semiconductor device, as supported throughout the specification.

No new matter has been added by the above amendment. Claims 1 and 3-10 are now pending in the application.